

Advance Technical Information

PolarP2[™] Power MOSFET

IXTQ480P2

N-Channel Enhancement Mode Avalanche Rated Fast Intrinsic Diode



$V_{\scriptscriptstyle \sf DSS}$	=	500V
D ₂₅	=	52A
R _{DS(on)}	≤	$120 \mathrm{m}\Omega$
t _{rr(typ)}	=	400ns

Symbol	Test Conditions	Maximum Ratings		
V _{DSS} V _{DGR}	$T_J = 25^{\circ}\text{C to } 150^{\circ}\text{C}$ $T_J = 25^{\circ}\text{C to } 150^{\circ}\text{C}, R_{GS} = 1\text{M}\Omega$	500 500	V	
V _{GSS} V _{GSM}	Continuous Transient	± 30 ± 40	V	
 _{D25} _{DM}	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 25^{\circ}{\rm C}$, Pulse Width Limited by $T_{\rm JM}$	52 150	A A	
I _A E _{AS}	$T_{c} = 25^{\circ}C$ $T_{c} = 25^{\circ}C$	52 1.5	A J	
dv/dt	$I_{_{S}} \le I_{_{DM}}, \ V_{_{DD}} \le V_{_{DSS}}, T_{_{J}} \le 150^{\circ}C$	10	V/ns	
P _D	T _c = 25°C	960	W	
T _J T _{JM} T _{stg}		-55 +150 150 -55 +150	°C °C °C	
T _L T _{SOLD}	Maximum Lead Temperature for Soldering Plastic Body for 10s	300 260	°C °C	
M _d	Mounting Torque	1.13/10	Nm/lb.in.	
Weight		5.5	g	

TO-3P		
	G D S	Tab

G = Gate	D	=	Drain
S = Source	Tab	=	Drain

Features

- Avalanche Rated
- Fast Intrinsic Diode
- Dynamic dv/dt Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

		cteristic Values			
$(T_J = 25^{\circ}C,$	Unless Otherwise Specified)	Min.	Тур.	Max.	
BV _{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	500			V
V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5		4.5	V
I _{gss}	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA
I _{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$			5	μΑ
	$T_J = 125^{\circ}C$;		50	μΑ
R _{DS(on)}	$V_{GS} = 10V, I_{D} = 0.5 \bullet I_{D25}, \text{ Note 1}$			120	mΩ

TO-3P (IXTQ) Outline



Symbol	Symbol Test Conditions Char		acteristic Values	
$(T_J = 25^{\circ}C U$	nless Otherwise Specified)	Min.	Тур.	Max.
g _{fs}	$V_{DS} = 20V, I_{D} = 0.5 \bullet I_{D25}, Note 1$	30	48	S
C _{iss}			6800	pF
C _{oss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		680	pF
C _{rss}			44	pF
t _{d(on)}	Resistive Switching Times		22	ns
t _r	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$		11	ns
t _{d(off)}	00 50 500 5		40	ns
t _f			8	ns
$Q_{g(on)}$			108	nC
Q _{gs}	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$		37	nC
Q_{gd}			38	nC
R _{thJC}				0.13 °C/W
R _{thCS}			0.25	°C/W

Source-Drain Diode

Symbol Test Conditions		Characteristic Values			
$(T_J = 25^{\circ}C U$	nless Otherwise Specified)	Min.	Тур.	Max.	
I _s	$V_{GS} = 0V$			52	Α
I _{SM}	Repetitive, Pulse Width Limited by $\rm T_{_{\rm JM}}$			204	Α
V _{SD}	$I_F = I_S$, $V_{GS} = 0V$, Note 1			1.5	V
t _{rr}	$I_F = 26A$, -di/dt = 100A/ μ s		400		ns
	$V_{R} = 100V, V_{GS} = 0V$				

Note 1. Pulse test, $t \le 300\mu s$, duty cycle, $d \le 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.